

Supplement information for “Lattice Distortion-Enhanced Superlubricity of (Mo, X)S₂ (X= Al, Ti, V and Cr) with Moiré Superlattice”

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The 2D contour plots of bonding charge density of pure MoS₂ with the twisted angles of 13.17°, 21.79° and 32.20°, respectively are shown in Fig. S1., which indicates the movement of interlayer S atoms. Interlayer S-S repulsion in the AA stacking, where the top layer S atom sits almost above a bottom layer S atom, is improved, and in AB stacking (Bernal stacking) area are weakened. This change of intralayer Mo-S bonds generates the layer corrugations in Fig. S2.. Thus, the larger twisted angles in the period range of 0°~30°, the smaller areas of AA stacking are formed which results in the low corrugations of layers, corresponding to the previous studies¹⁻².

Fig. S3-Fig. S5 display the 2D contour plots and 3D isosurface of bonding charge density of non-twisted (Mo, X)S₂ (X= Al, Ti, V and Cr). It is acknowledged that van der Waals (vdW) interactions is influenced by the polarizable bond. On the one hand, the p-type doping for Al, Ti and V result in less polarizable S atoms in the interface layer and lower vdW interactions between interlayer³⁻⁵. On the other hand, the electronegativity difference of X-S (X= Al, Ti, V and Cr) is larger than Mo-S, which implies the stronger polarization of X-S. Since interlayer balance between the S-S hybridization and vdW interactions are broken by the above two competitive factors, atoms are impelled in the direction of perpendicular 2D-plane and the layer deformations are formed. Due to the less polarizable S atoms at the interface for (Mo, X)S₂ (X= Al, Ti), the vdW force decreases and the doped positions peaks at Mo atom layer. Especially, a few bonding charge around the p-orbital element of Al in Fig. S3, indicates extreme weak bonding strength, resulting drastic fluctuation of Mo layer. Fig. S4 shows that the Cr atom is pushed at the bottom point of Mo atom layer owing to the larger vdW attractions by stronger polarizable bonds of Cr-S (1.66-2.58 for Cr-S and 2.16-2.58 for Mo-S, respectively). The V atom also locates at the bottom of Mo layer, which could be attributed to the effect of electronegativity difference is higher than p-type doping.

The schematic diagram of the deposition process for (Mo, X)S₂ (X=Al, Ti, V, Cr) with non-twisted as shown in Fig. S6. In addition, the originally experimental data and computational structures have been attached in separate files.

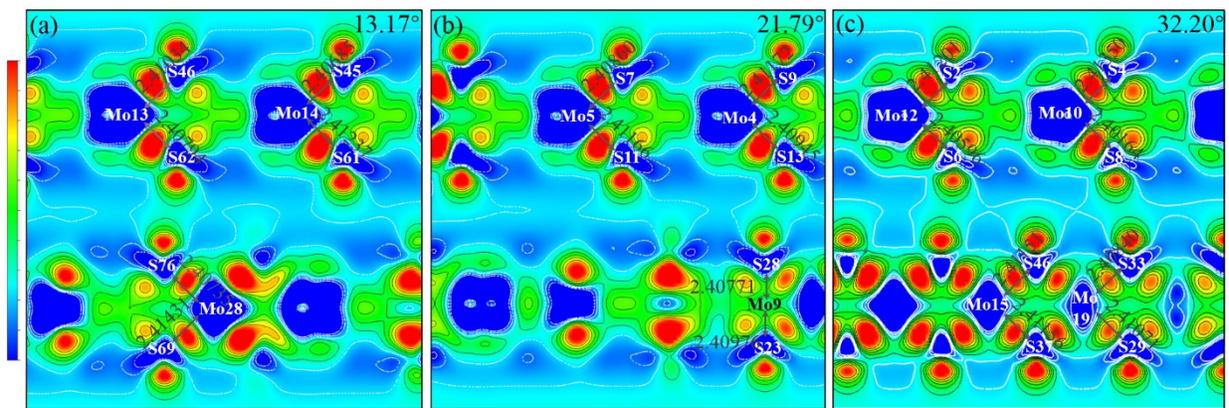


Fig. S1 The 2D contour plots of bonding charge density ($\Delta\rho$) of the twisted angle of 13.17°, 21.79° and 32.20° MoS₂. The bonding length of Mo-S, Mo and S atoms in feature sites are labelled and $\Delta\rho = -0.0005\sim 0.013e^{-1}\text{\AA}^{-3}$.

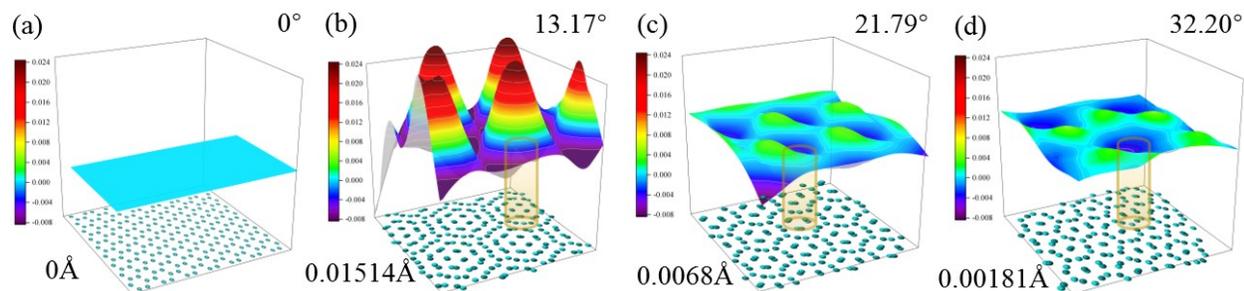


Fig. S2 The corrugation of Mo-atom in the up layer along the direction of z axis. (a) is the as-built pure-0° MoS₂, and (b-d) show the twisted angle of 13.17°, 21.79° and 32.20° MoS₂, respectively.

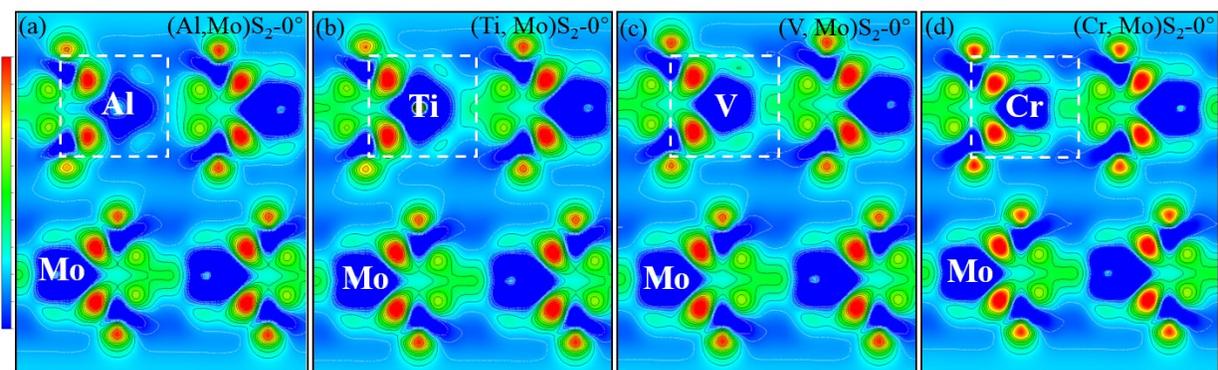


Fig. S3 The 2D contour plots of bonding charge density ($\Delta\rho$) of (a) (Al, Mo)S₂-0°, (b) (Ti, Mo)S₂-0°, (c) (V, Mo)S₂-0° and (d) (Cr, Mo)S₂-0° structures. The X (X=Al, Ti, V, Cr) and Mo atoms in feature sites are labelled and of $\Delta\rho = -0.005 \sim 0.018 e^{-1} \text{Å}^{-3}$.

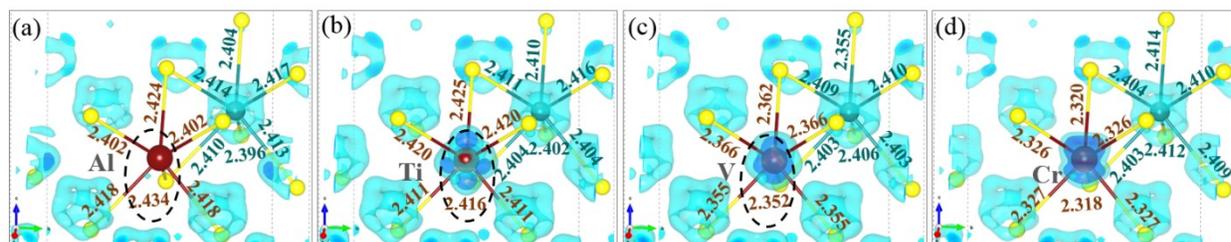


Fig. S4 3D isosurfaces of $\Delta\rho$ are applied to characterize the non-twisted (Mo, X)S₂ (X= Al, Ti, V and Cr). The $\Delta\rho = -0.02, -0.03 e^{-1} \text{Å}^{-3}$ isosurface are plotted in cyan and blue colors respectively, which identify the atomic sites contributing electrons ($\Delta\rho < 0$). The bonding length of Mo-S and X-S (X=Al, Ti, V, Cr) are labelled.

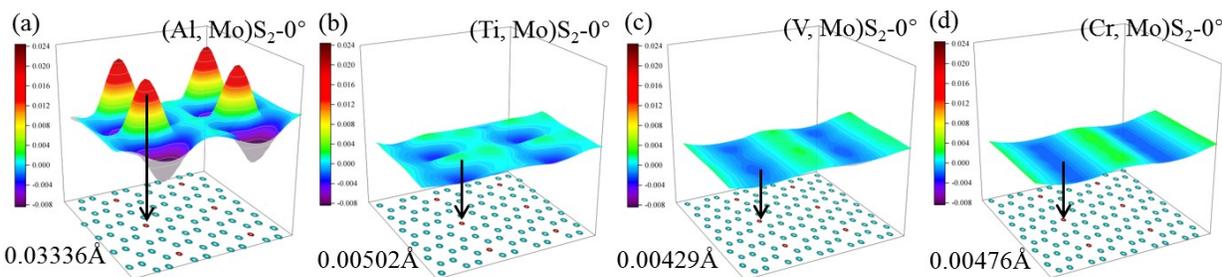


Fig. S5 The corrugation of Mo-atom in the up layer of non-twisted (Mo, X)S₂ (X= Al, Ti, V and Cr) along the z axis direction.

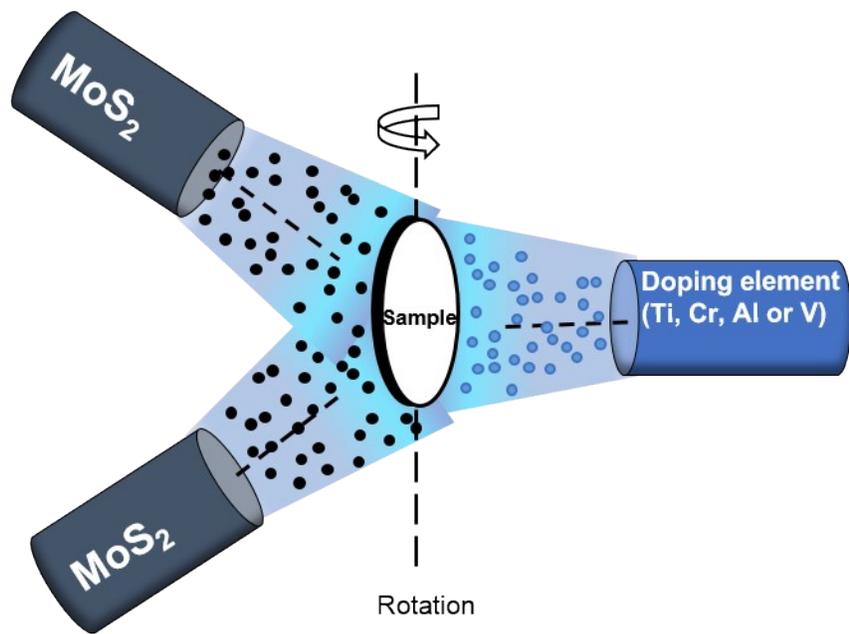


Fig. S6 Schematic diagram of the deposition process for $(\text{Mo}, \text{X})\text{S}_2$ ($\text{X} = \text{Al}, \text{Ti}, \text{V}, \text{Cr}$) with non-twisted in this work.

Reference

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